TOSHIBA INSULATED GATE BIPOLAR TRANSISTOR SILICON N CHANNEL IGBT

GT20J301

HIGH POWER SWITCHING APPLICATIONS MOTOR CONTROL APPLICATIONS

• Third-generation IGBT

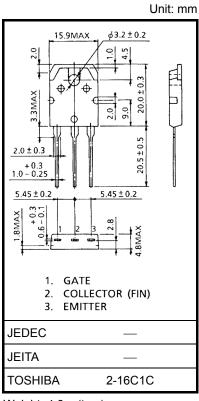
• Enhancement mode type

• High speed : $t_f = 0.30\mu s$ (Max.) • Low saturation voltage : VCE (sat) = 2.7V (Max.)

• FRD included between emitter and collector

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT	
Collector-Emitter Voltage		V _{CES}	600	V	
Gate-Emitter Voltage		V _{GES}	±20	V	
Collector Current	DC	Ic	20	Α	
	1ms	ICP	40	Α	
Emitter-Collector Forward Current	DC	lF	20	Α	
	1ms	I _{FM}	40	Α	
Collector Power Dissipation (Tc = 25°C)		PC	130	W	
Junction Temperature		Tj	150	°C	
Storage Temperature Range		T _{stg}	-55~150	°C	



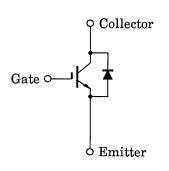
Weight: 4.6 g (typ.)

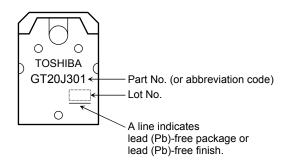
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

EQUIVALENT CIRCUIT

MARKING

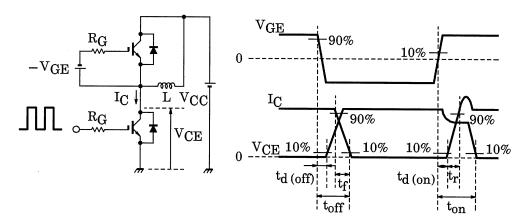




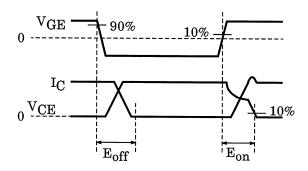
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

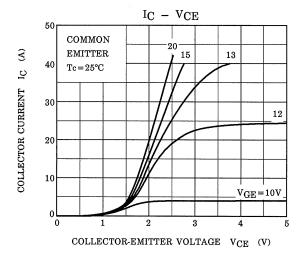
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT
Gate Leakage Current		I _{GES}	V _{GE} = ±20V, V _{CE} = 0	_	_	±500	nA
Collector Cut-Off Current		I _{CES}	V _{CE} = 600V, V _{GE} = 0	_	_	1.0	mA
Gate-Emitter Cut-Off Voltage		V _{GE} (OFF)	I _C = 2mA, V _{CE} = 5V	5.0	_	8.0	V
Collector-Emitter Saturation Voltage		V _{CE} (sat)	I _C = 20A, V _{GE} = 15V	_	2.1	2.7	V
Input Capacitance		C _{ies}	V _{CE} = 20V, V _{GE} = 0, f = 1MHz	_	1450	_	pF
Switching Time	Rise Time	t _r	Inductive Load V_{CC} = 300V, I_{C} = 20A V_{GG} = ±15V, R_{G} = 56 Ω (Note)	_	0.12	_	- µs
	Turn-On Time	t _{on}		_	0.40	_	
	Fall Time	t _f		_	0.15	0.30	
	Turn-Off Time	t _{off}		_	0.70	_	
Peak Forward Voltage		V _F	I _F = 20A, V _{GE} = 0	_	_	2.0	V
Reverse Recovery Time		t _{rr}	I _F = 20A, di / dt = -100A / μs	_	_	200	ns
Thermal Resistance (IGBT)		R _{th (j−c)}	_	_	_	0.96	°C / W
Thermal Resistance (Diode)		R _{th (j−c)}	_	_	_	2.5	°C / W

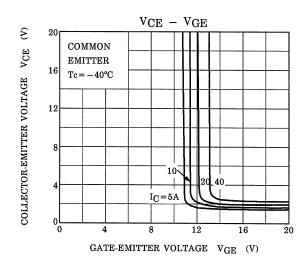
Note: Switching time measurement circuit and input / output waveforms

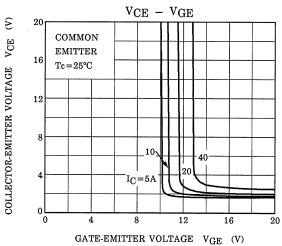


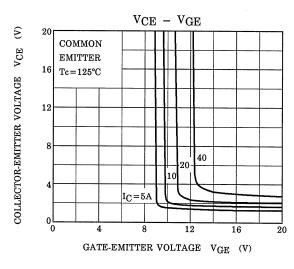
Switching loss measurement waveforms

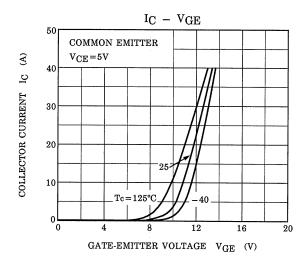


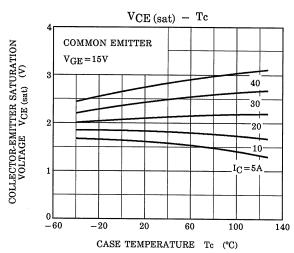




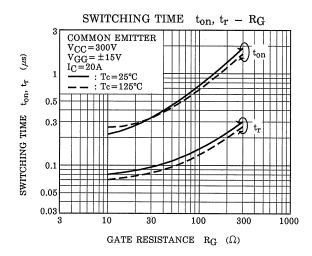


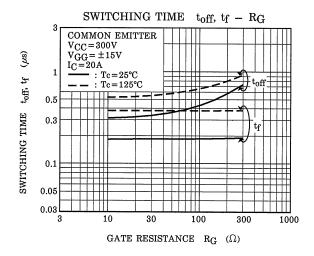


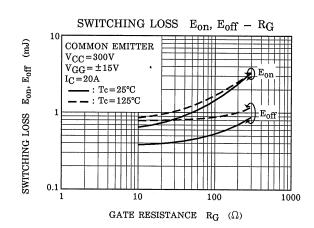


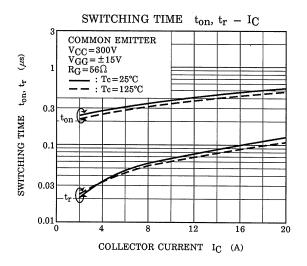


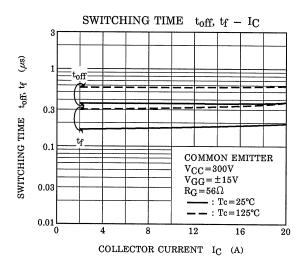
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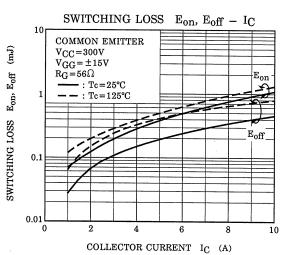


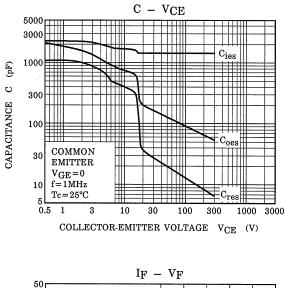


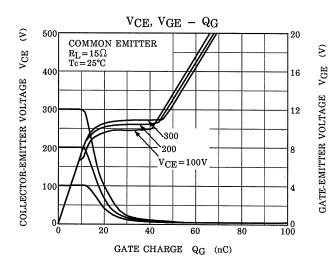


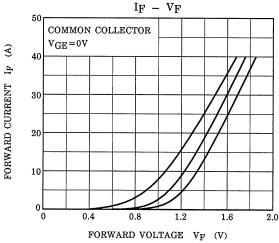


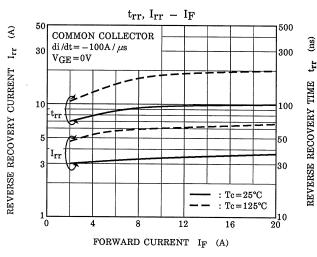


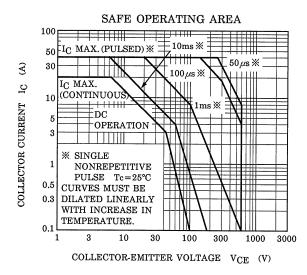


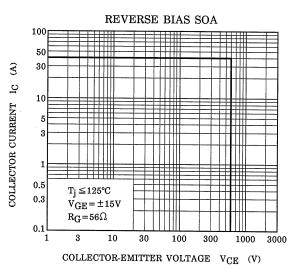




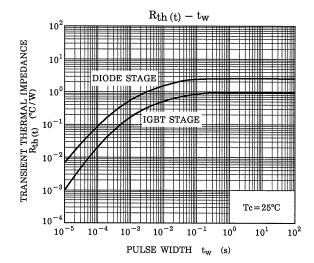








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